

A product Line of Diodes Incorporated

PI3DPX1203

DisplayPort 1.4 Linear ReDriver for Source, Active Cable & Sink-side Applications

Description

Pericom's PI3DPX1203 is the Displayport compliant, up to 4 channel, 8.1 Gbps Linear Redriver with Link Training transparency support. Displayport source-side and sink-side devices communicate through the AUX transaction between the source and the sink-side devices.

Input Equalization, Voltage Swing and Flat Gain control can configure with pin-strapping or I2C programing to optimized Main Link high speed signals over a variety of physical medium by reducing inter-symbol interference. Pericom's Linear Redriver technology can deliver 2 times better additive jitters performance than traditional Redrivers.

Linear Equalizer always provide very flexible component placement, cascade connection and easy adjustment after the Redriver location changes during the product development events.

Features

- → Compliant with VESA DisplayPort 1.4 specification up to 10 Gbps Link Rate
- ➔ Linear ReDriver allows flexible placement with Main Link boost setting
- ➔ Ideal for DP/USB Type-C Source and Sink-side application with PD Controllers with Aux Link Training Transparent Mode support
- → Linear Equalizer Increases Main Link Margin with sink-side DFE (Decision Feedback Equalizer)
- ➔ Independent Main Link channel configuration for 4-bit Equalization, 2-bit Voltage Output swing and 2-bit Flat Gain control
- ➔ Pin strap or I2C programmable for device Configuration setting
- → Intra- and Inter-Channel Polarity swap support
- → I2C Address selectable for configuration register access
- ➔ Power Supply Voltage: 3.3V

Applications

- → Display, Monitors
- → Active Adaptors, Dongles, Docking
- ➔ Notebook, DeskTop, AIO PC

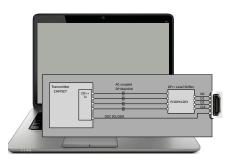


Figure 1-1. DP1.4 ReDriver in the NB PC

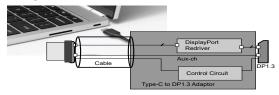


Figure 1-2. ReDriver in the DP1.4 Type-C Dongle

Ordering Information

Ordering Number	Package Code	Package Description
PI3DPX1203 Zhex	ZH	42-pin, Very Thin Quad Flat No-Lead (TQFN), Tray Type W24
PI3DPX1203 ZHE+DRX	ZH	42-pin, Very Thin Quad Flat No-Lead (TQFN), Type W16

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/ EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/

3. E = Pb-free and Green

4. X suffix = Tape/Reel





2. General Information

2.1 Revision History

Date	Description of Changes			
May 2016	In Functional/Application, informative data added for system design supports			
July 2016	In application session, Evaluation board reference schematic removed			
Apr 2017	Add Tape/Reel Package W16 in Product Brief Ordering Information			
Jun 2017	Power-up sequence added in the functional description			
Jan 2018	Changed for DP 1.4 8.1Gbps support. Added package marking information. In Application session, updated reference schematics and DP 1.4 CTS test report			

2.2 Related Products

Part Numbers	Products Description
Retimers / Jitter Cleaner	
PI3HDX2711B	HDMI 2.0 and DP++ Retimer (Jitter Cleaner)
PI3HDX711B	HDMI 1.4 and DP++ ReTimer (Jitter Cleaner)
Redrivers	
PI3DPX1203B	DisplayPort 1.4 Redriver for Source/Sink/Cable Application, Linear-type
PI3HDX1204B1	HDMI 2.0 Redriver (DP++ Level Shifter), High EQ, place near to the source-side, Limiting type
PI3HDX1204E	HDMI 2.0 Linear Redriver (DP++ Level Shifter) , Link transparent, place near to the sink-side
PI3DPX1207B	DisplayPort 1.4 Alt Type-C Redriver, 8.1 Gbps and USB3.1 10 Gbps, Link Transparent
PI3DPX1202A	Low Power DisplayPort 1.2 Redriver with built-in AUX Listener, Limiting-type
PI3HDX511F	High EQ HDMI 1.4b Redriver and DP++ Level Shifter for Sink/Source Application, Limiting-type
Active Switches & Splitte	rs
PI3DPX1205A	DisplayPort 1.4 Alt Type-C Mux Redriver, 8.1 Gbps and USB3.1 10 Gbps, Link Transparent
PI3HDX231	HDMI 2.0 3:1 ports Mux Redriver, Linear-type
PI3HDX414	HDMI 1.4b 1:4 Demux Redriver & Splitter for 3.4 Gbps Application, Limiting-type
PI3HDX412BD	HDMI 1.4b 1:2 Demux Redriver & Splitter for 3.4 Gbps Application, Limiting-type
PI3HDX621	HDMI 1.4 Redriver 2:1 Active Switch with built-in ARC and Fast Switching support, Limiting-type



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PI3DPX1203

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3. Pinout

3.1 Package Pinout (Top View)

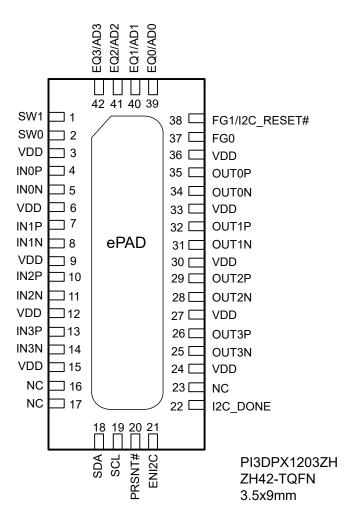


Figure 3-1. 42-TQFN package pin-out

Note: High-speed data channels support inter-channel polarity and inter-channel order swap.





3.2 Pin Description

Pin Name	Pin #	Туре	Description			
IN0P/N	4, 5	Ι	CML Inputs +/- for Channel A0 with internal 50 Ω pull-up, and 200k Ω pull-up for power down mode			
IN1P/N	7, 8	Ι	CML Inputs +/- for Channel A1 with internal 50 Ω pull-up, and 200k Ω pull-up for power down mode			
IN2P/N	10, 11	Ι	CML Inputs +/- for Channel A2 with internal 50 Ω pull-up, and 200k Ω pull-up for power down mode			
IN3P/N	13, 14	Ι	CML Inputs +/- for Channel A3 with internal 50 Ω pull-up, and 200k Ω pull-up for power down mode			
OUT0P/N	35, 34	0	CML Outputs +/- for Channel A0 with internal 50 Ω pull-up, and 2k Ω pull-up for power down mode			
OUT1P/N	32, 31	0	CML Outputs +/- for Channel A1 with internal 50 Ω pull-up, and 2k Ω pull-up for power down mode			
OUT2P/N	29, 28	0	CML Outputs +/- for Channel A2 with internal 50 Ω pull-up, and 2k Ω pull-up for power down mode			
OUT3P/N	26, 25	0	CML Outputs +/- for Channel A3 with internal 50 Ω pull-up, and 2k Ω pull-up for power down mode			
SDA	18	I/O	I ² C Data			
SCL	19	I/O	I ² C Clock			
PRSNT#	20	I	Cable Present Detect Input. This pin has internal $100k\Omega$ pull-up. When the pin is "1", the cable does not present and enter to the lower power mode. When the pin is "0", the device is Active with normal operation.			
ENI2C	21	Ι	I2C enable pin. When the pin is "1", register access I2C Slave mode When the pin is "FLOAT/Middle", read external EEPROM Master mode. Middle(M) is 50% of VDD. When the pin is "0", pin-strapping control mode			
I2C_DONE	22	0	Valid register load status output. Use for the daisy chain master "0" = External EEPROM load failed "1" = External EEPROM load passed			
SW[1:0]	1, 2	Ι	Swing Control 2 bits. Input with internal 100 k Ω pull-up. This pin control the output Voltage Swing Level in all channel when ENI2C is "0".			
FG0	38, 37	Ι	Flat Gain Control 2 bits pins. Inputs with internal 100 k Ω pull-up. This pin control the output flat gain level on all channels when ENI2C is "0".			
FG1/I2C_RE- SET#	38	Ι	I2C Reset pin. Active "0". All programmable registers reset to the default state. Inputs with internal $100k\Omega$ pull up.			
EQ[3:0]/ AD[3:0]	42, 41, 40, 39	Ι	EQ setting pins. Inputs with internal 100 k Ω pull-up. This 4-bit pins control the amount of Input Equalizer Boost in all channel, when ENI2C is "0". Or I ² C address control 4 bits with internal 100k Ω pull-up.			
NC	16,17,23	NC	No Connect			





Pin Name	Pin #	Туре	Description
VDD	3,6,9,12, 15,24,27, 30,33,36	PWR	3.3V Power Supply
GND	Center Pad	GND	Exposed Ground pad





4. Functional

4.1 Functional Block Diagram

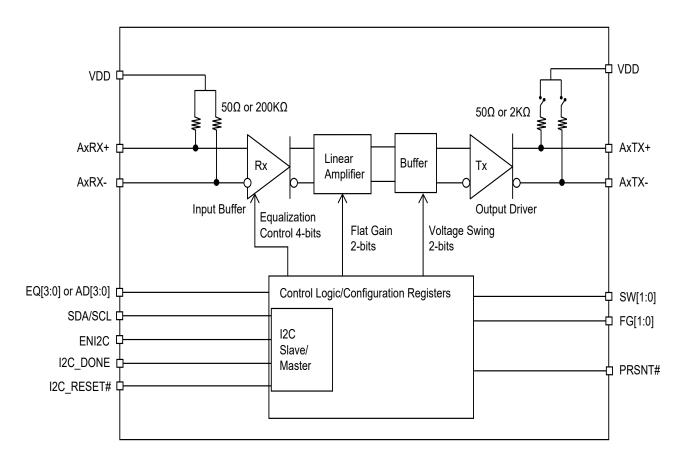


Figure 4-1. PI3DPX1203 Block Diagram



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4.2 Function Description

4.2.1 Power-up Timing

After PRSNT# signal is properly set, power up timing sequence complete. PRSNT signal from controller must be low until power supply become stable.

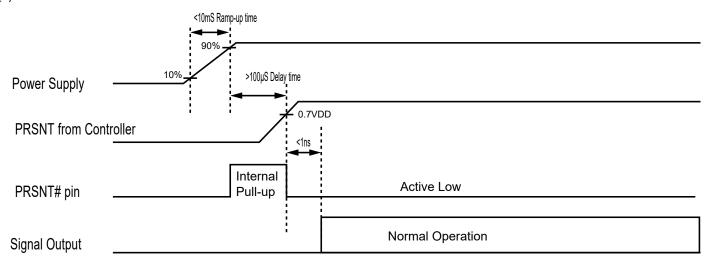
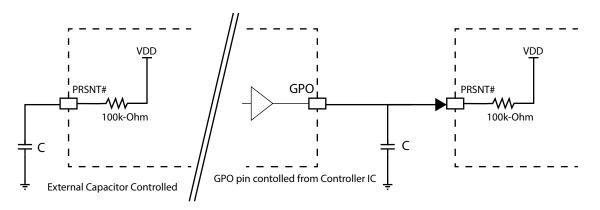


Figure 4-1 Power-up timing Sequence

4.2.2 Reset Implementation

When PRSNT# is high, the device is power-down mode and outputs are high impedance. It is critical to transition the PRSNT#, after the power supply VDD has reached the minimum recommended operation voltage. This can be achieved by the control signal GPO or by an external capacitor connected to GND.

To insure properly reset, the PRSNT# pin must be de-asserted for at least 100µS before re-asserted, and must be reprogrammed in I2C mode. When using external capacitor, the size of the cap value depends on the power-up VDD supply ramp. Larger value results in a slower ramp-up time. Consider 0.1µF capacitor is recommended as a reasonable first estimate.









4.2.3 Power-down Mode

Power-down mode can be controlled by the pin-strapping or I2C programming. When Cable Present Detection pin PRSNT# is set to HIGH, it enters into the power-down mode. Input and Output termination resistors set to 200 k Ω and 2 k Ω pull-up respectively.

PRSNT#	Description	Input Termination Resistor	Output Termination Resistor
Н	Power-down mode. PRSNT# is internally pull-up 100 k Ω .	200 kΩ pull-up	2 kΩ pull-up
L	Active Low for normal operation	50 Ω pull-up	50 Ω pull-up

4.2.4 Output -1 dB Compression Setting

Swing Control 2 bits SW[1:0] can control the linearity of the output voltage, when input amplitude changes.

SW1	SW0	mVppd @ 8 Gbps
0	0	700
0	1	800
1	0	900
1	1	1000

4.2.5 Flat Gain Setting

Flat Gain Control 2 bits FG[1:0] are the selection bits for the DC value.

FG1	FG0	Gain
0	0	-4 dB
0	1	-2 dB
1	0	+0 dB
1	1	+2 dB





4.2.6 EQ Setting

Input EQ control 4 bits EQ[3:0] are the selection pins for the equalization selection of each Main Link channel.

EQ3	EQ2	EQ1	EQ0	8 Gbps Input EQ(dB)
0	0	0	0	3.3
0	0	0	1	3.8
0	0	1	0	4.3
0	0	1	1	4.8
0	1	0	0	5.4
0	1	0	1	5.8
0	1	1	0	6.3
0	1	1	1	6.8
1	0	0	0	7.2
1	0	0	1	7.7
1	0	1	0	8.1
1	0	1	1	8.5
1	1	0	0	8.9
1	1	0	1	9.2
1	1	1	0	9.6
1	1	1	1	9.9

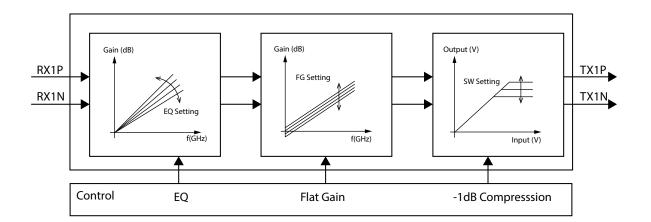


Figure 4-3 Illustration of EQ, Gain and Swing setting





5. I2C Programming

5.1 I2C Registers

I2C Address assignment							
A6 A5 A4 A3 A2 A1 A0 R/W							R/W
Address Byte 1 1 AD3 AD2 AD1 AD0 1=R, 0=W							1=R, 0=W

BYTE 0						
Bit	Туре	Power up condition	Description	Control affected	Comment	
7:0	Reserved				· ·	
BYTE 1						
Bit	Туре	Power up condition	Description	Control affected	Comment	
7:0	Reserved					
BYTE 2				1	I	
Bit	Туре	Power up condition	Description	Control affected	Comment	
7	R/W	0		A3 Power down		
6	R/W	0		A2 Power down		
5	R/W	0		A1 Power down		
4	R/W	0		A0 Power down		
3	R/W	0		Reserved	1 = Power dowr	
2	R/W	0		Reserved		
1	R/W	0		Reserved		
0	R/W	0		Reserved		
BYTE 3						
Bit	Туре	Power up condition	Description	Control affected	Comment	
7	R/W	0		EQ3		
6	R/W	0		EQ2	E li	
5	R/W	0		EQ1	Equalizer	
4	R/W	0	Channel AO and formation	EQ0		
3	R/W	0	- Channel A0 configuration	FG1		
2	R/W	0		FG0	Flat gain	
1	R/W	0		SW1	Surine	
0	R/W	0		SW0	Swing	





BYTE 4					
Bit	Туре	Power up condition	Description	Control affected	Comment
7	R/W	0		EQ3	
6	R/W	0		EQ2	F 1'
5	R/W	0		EQ1	Equalizer
4	R/W	0	Channel A1 configuration	EQ0	
3	R/W	0		FG1	Plat asia
2	R/W	0		FG0	Flat gain
1	R/W	0		SW1	Sturing
0	R/W	0		SW0	Swing
BYTE 5					
Bit	Туре	Power up condition	Description	Control affected	Comment
7	R/W	0		EQ3	
6	R/W	0		EQ2	
5	R/W	0	Channel A2 configuration	EQ1	Equalizer
4	R/W	0		EQ0	
3	R/W	0		FG1	Plat asia
2	R/W	0		FG0	Flat gain
1	R/W	0		SW1	Swing
0	R/W	0		SW0	Swing
BYTE 6					
Bit	Туре	Power up condition	Description	Control affected	Comment
7	R/W	0		EQ3	
6	R/W	0		EQ2	—— Equalizer
5	R/W	0		EQ1	
4	R/W	0	- Channel A3 configuration	EQ0	
3	R/W	0		FG1	
2	R/W	0		FG0	riat gain
1	R/W	0		SW1	Swing
0	R/W	0		SW0	Swing
BYTE 7					
Bit	Туре	Power up condition	Description	Control affected	Comment
7:0	Reserved				





5.2 I2C Operation

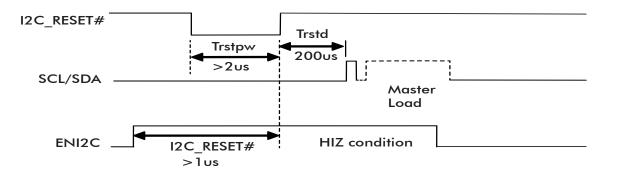
The integrated I2C interface operates as a master or slave device depending on the pin ENI2C being HIZ or HIGH respectively. Standard I2C mode (100 Kbps) is supported with 7-bit addressing. The data byte format is 8-bit.

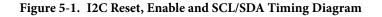
In the slave mode (ENI2C = "HIGH"), the device supports Read/Write. The bytes must be accessed in sequential order from the lowest to the highest byte with the ability to stop after any complete byte has been transferred.

Address bits A3 to A0 are programmable to support multiple chips environment. The Data is loaded, until a Stop sequence is issued. Master mode (ENI2C = HIZ) supports up to 16 masters connected in daisy chain through connecting I2C_DONE pin to I2C_RESET# pin of the next part.

Tuble 5-1. Muster LET KOM und starting address for device address							
I2C address: AD[3:0]	Data starting location	I2C address: AD[3:0]	Data starting location				
0000	00H	1000	80H				
0001	10H	1001	90H				
0010	20H	1010	A0H				
0011	30H	1011	B0H				
0100	40H	1100	С0Н				
0101	50H	1101	D0H				
0110	60H	1110	ЕОН				
0111	70H	1111	F0H				

 Table 5-1. Master EEPROM data starting address for device address





Transferring Data

Every byte put on the SDA line must be 8-bit long. Each byte has to be followed by an acknowledge bit. Data is transferred with the most significant bit (MSB) first (see the I2C Data Transfer diagram). It will never hold the clock line SCL LOW to force the master into a wait state.





Acknowledge

Data transfer with acknowledge is required from the master. When the master releases the SDA line (HIGH) during the acknowledge clock pulse, it will pull down the SDA line during the acknowledge clock pulse so that it remains stable LOW during the HIGH period of this clock pulse as indicated in the I2C Data Transfer diagram. It will generate an acknowledge after each byte has been received.

Data Transfer

A data transfer cycle begins with the master issuing a start bit. After recognizing a start bit, it will watch the next byte of information for a match with its address setting. When a match is found it will respond with a read or write of data on the following clocks. Each byte must be followed by an acknowledge bit, except for the last byte of a read cycle which ends with a stop bit. Data is transferred with the most significant bit (MSB) first.

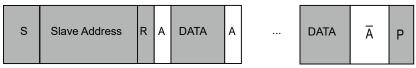
Start & Stop Conditions

A HIGH to LOW transition on the SDA line while SCL is HIGH indicates a START condition. A LOW to HIGH transition on the SDA line while SCL is HIGH defines a STOP condition, as shown in the figure below

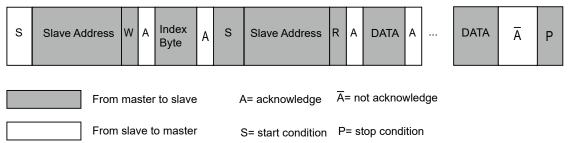
. _

Write S	Sequence									
S	Slave Address	W	A	Index Byte	A	DATA	A	 DATA	A	Ρ

Read Sequence



Combined Sequence



Notes:

- 1. Only Block read and Block write from the lowest byte are supported for this application.
- 2. For some I2C application, an offset address byte will be presented at the second byte in write command, which is called dummy byte, and will be simply ignored in this application for correct interoperation.





6. Electrical Specification

6.1 Absolute Maximum Ratings

Storage Temperature	–65 °C to +150 °C
Supply Voltage to Ground Potential	-0.5 V to +4.6 V
DC SIG Voltage	
Output Current	
Power Dissipation Continuous	
ESD, HBM	
Maxumum junction Temperature	

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

6.2 Recommended Operating Conditions⁽¹⁾

Parameter ⁽¹⁾	Min.	Тур.	Max	Units
Power supply voltage (VDD to GND)	3.0	3.3	3.6	V
Supply Noise Tolerance (from 100KHz to 10MHz)		100		mVp-p
Ambient Temperature	-40	25	85	°C

(1) Typical parameters are measured at VCC = 3.3 ± 0.3V, TA = 25°C. They are for reference purposes, and are not production-tested

6.3 Power Consumption

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
VDD	Power supply voltage		3.0	3.3	3.6	V
IDD	Power supply current	SW[1:0]=11, VDD = 3.6 V		260	360	mA
IDDQ	Standby current	All other control pins are open		2.0	4.2	mA

6.4 AC/DC Characteristics

6.4.1 LVCMOS I/O DC Specifications

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
VIH	DC input logic HIGH		VDD/2 + 0.7		VDD + 0.3	V
VIL	DC input logic LOW		-0.3		VDD/2 - 0.7	V
VOH	At IOH = $-200 \ \mu$ A		VDD + 0.2			V
VOL	At IOL = -200 μA				0.2	V
Vhys	Hysteresis of Schmitt trigger input		0.8			V





6.4.2 Main Link Differential

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{RX-DIF-} Fp-p	Peak to peak differential input voltage	For HBR		200 ⁽¹⁾		mV
V _{ODO}	Differential overshoot voltage				15% *VDD	V
V _{ODU}	Differential undershoot voltage				25% *VDD	V
I _{OFF}	Single end standby current				10	μA
I _{SC}	Output short current				60	mA
Gp		EQ[3:0] = 1111 EQ[3:0] = 1000 EQ[3:0] = 0000		9.9 7.2 3.3		dB
	100 mVp-p sine wave input	Variation around typical	-3		+3	dB
	Flat gain: 100 MHz, EQ[3:0] = 1000, SW[1:0] = 10	FG[1:0] = 11FG[1:0] = 10FG[1:0] = 01FG[1:0] = 00		2 0 -2 -4		dB
		Variation around typical	-3		+3	dB
V _{1dB_100M}	-1 dB compression point of output swing at 100 MHz	SW[1:0] = 11 SW[1:0] = 10 SW[1:0] = 01 SW[1:0] = 00		1370 1280 1040 920		mVppd
C _{RX}	RX AC coupling capacitance			220		nF
011	I (2)	10 MHz to 4.1 GHz differential		-13.0		ID
S11	Input return loss ⁽²⁾	1 GHz to 4.1 GHz common mode		-5.0		- dB
S22	Output return loss ⁽²⁾	10 MHz to 4.1 GHz differential		-15		dB
322	Output leturn loss	1 GHz to 4.1 GHz common mode		-6.0		ub
D	DC single-ended input imped- ance			50		
R _{IN}	DC Differential Input Imped- ance			100		Ω
D	DC single-ended output im- pedance			50		
R _{OUT}	DC Differential output Imped- ance			100		Ω
Z _{RX-HIZ}	DC input impedance during reset or power down			200		kΩ
t _{PD}	Latency	From input to output		0.5		ns

Note:

(1) Please refer more data in the VIN/VOUT plot. VOUT changes with EQ and FG setting. Both the Redriver and the Sink device system should be carefully designed to ensure sink-device compliance.





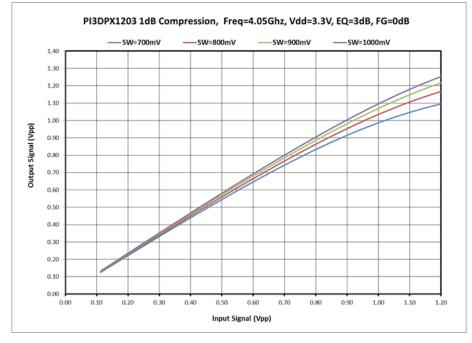


Figure 6-1. -1dB Compression(Voltage Sweep) between 0 to 600mV Inputs @ 8Gbps

(2) Measured using a vector-network analyzer (VNA) with -15dBm power level applied to the adjacent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with 50Ω .

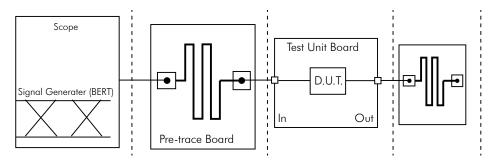
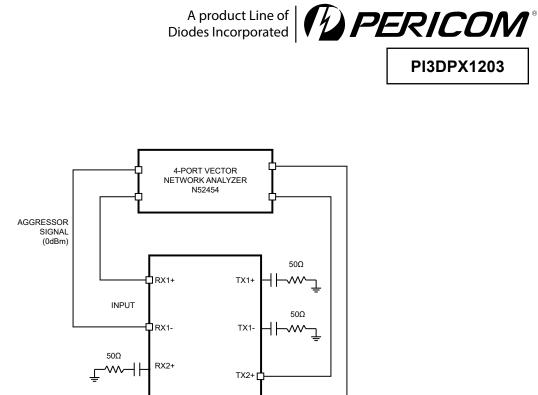


Figure 6-2. AC Electrical Measurement Test Setup





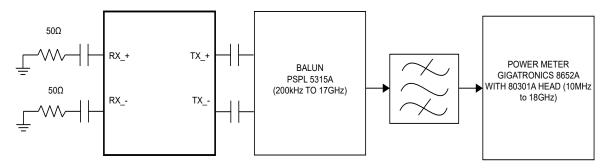
OUTPUT

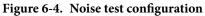
TX2-

Figure 6-3. Channel-isolation test configuration

RX2-

50Ω







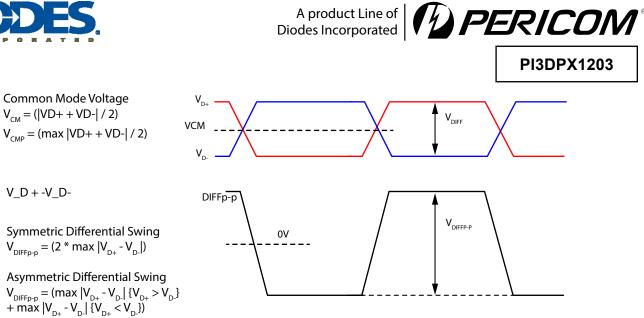


Figure 6-5. Definition of Differential Voltage and Differential Voltage Peak-to-Peak

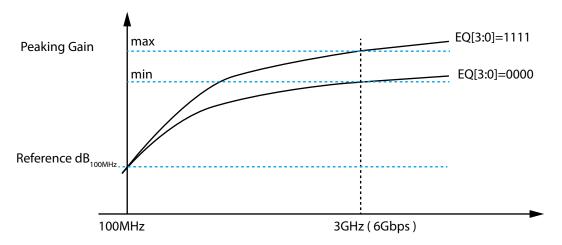


Figure 6-6. Definition of Peaking Gain relative to 100MHz, 100mVp-p sine wave input





6.4.3 SCL/SDA Specification for I2C BUS

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
SDA and S	CL I/O for I2C-bus	1	1 1			
VDD	Nominal Bus Voltage		3.0		3.6	V
V _{IH}	DC input logic HIGH		$V_{DD}/2 + 0.7$		V _{DD} + 0.3	V
V _{IL}	DC input logic LOW		-0.3		V _{DD} /2 - 0.7	V
V _{OL}	DC output logic LOW	$I_{OL} = 3mA$			0.4	V
t _{OF}	Output fall time from VIHmin to VILmax with bus cap. 10-400pF				250	ns
AC/DC Sp	ecifications - SCL/SDA for I2C BUS					
I _{PU}	Current Through Pull-Up Resistor or Current Source	High Power specification	3.0		3.6	mA
Ileak-bus	Input leakage per bus segment		-200		200	uA
Ileak-pin	Input leakage per device pin			-15		uA
CI	Capacitance for SDA/SCL				10	pF
f _{SCLK}	Bus Operation Frequency			100		KHz
tBUF	"Bus Free Time Between Stop and Start condition"		1.3			us
tHD:STA	Hold time after (Repeated) Start condition. After this period, the first clock is generated.	At Ipull-up, Max	0.6			us
tSU:STA	Repeated start condition setup time		0.6			us
tSU:STO	Stop condition setup time		0.6			us
tHD:DAT	Data hold time		0			ns
tSU:DAT	Data setup time		100			ns
tLOW	Clock Low period		1.3			us
tHIGH	Clock High period		0.6		50	us
tF	Clock/Data fall time				300	ns
tR	Clock/Data rise time				300	ns
tPOR	"Time in which a device must be operation after power-on reset"				500	ms

Note:

(1) Recommended value.

(2) Recommended maximum capacitance load per bus segment is 400pF.

(3) Compliant to I2C physical layer specification.

(4) Ensured by Design. Parameter not tested in production.

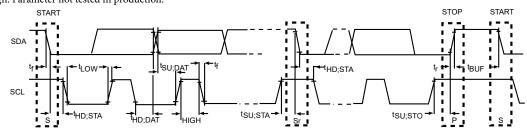


Figure 6-1 I2C Timing Diagram





6.5 Function Control vs. Output Signals (Informative)

6.5.1 Output Swing and Gain Information

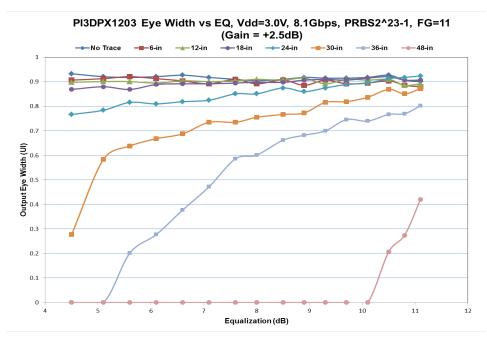


Figure 6-7. Eye Width vs EQ, Output Swing =1000mV, Gain=+2.5dB (Vin =800mVdiff)

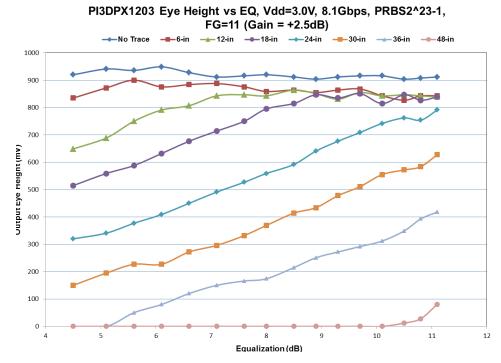
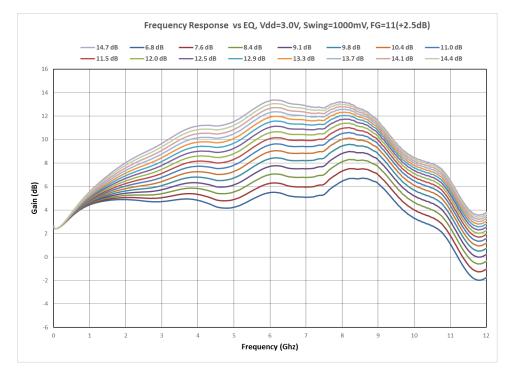
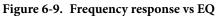


Figure 6-8. Eye Height vs EQ, Output Swing =1000mV, Gain=+2.5dB (Vin =800mVdiff)









Freq Response vs EQ, FG=11(+2.5dB), OutputSwing=1000mV, Vdd=3.0V, 25C Input Power=-15dBm, No Input Trace

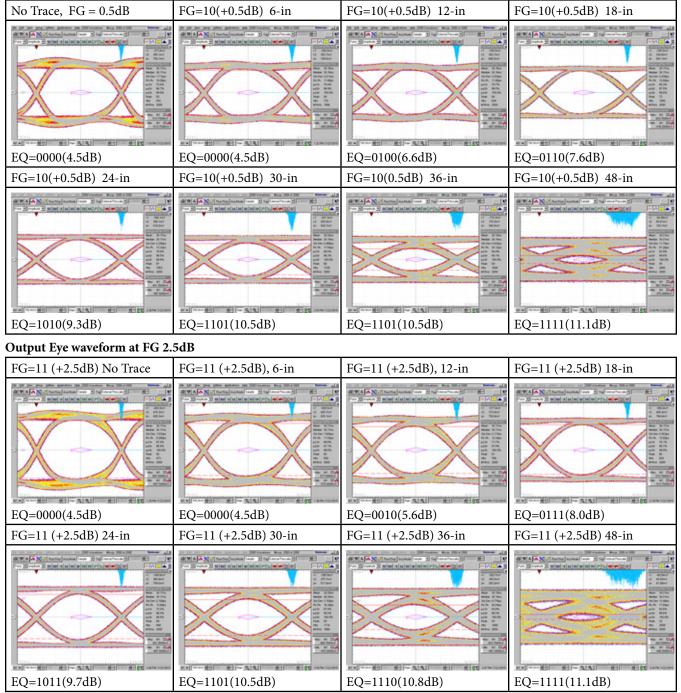


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6.6 Output Eye diagram, Trace length and EQ

Condition: Output Eye Opening with Input Equalization, 8.1 Gbps, Vdd=3.0V, 25C, Using PRBS 2^23-1 pattern, Input Swing=800mVd, Output Swing=1000mV

Output Eye waveform at FG 0.5dB



Note:

(1) Trace card insertion loss profile is shown below.





Frequency	3 GHz	6 GHz	Units
6 inch Input Trace	-1.43	-4	dB
12 inch Input Trace	-6.1	-11	dB
18 inch Input Trace	-8.34	-15	dB
30 inch Input Trace	-10.14	-18	dB
36 inch Input Trace	-12.13	-22	dB
48 inch Input Trace	-16.42	-29	dB



Figure 6-2 Trace board photo





6.7 IDD with different mode settings at VDD = 3.3V [Informative]

Test Conditions		IDD (mA)	IDD (mA)			
Control Setting	Gain (dB)	Swing(mV)	-40C	25C	90C	
FG/SW=0000	-3.5	700	199	216	226	
FG/SW=0001	-3.5	800	217	233	243	
FG/SW=0010	-3.5	900	234	250	260	
FG/SW=0011	-3.5	1000	251	267	276	
FG/SW=0100	-2.5	700	199	215	225	
FG/SW=0101	-2.5	800	217	232	242	
FG/SW=0110	-2.5	900	234	249	259	
FG/SW=0111	-2.5	1000	251	266	276	
FG/SW=1000	+0.5	700	199	215	224	
FG/SW=1001	+0.5	800	216	232	241	
FG/SW=1010	+0.5	900	233	249	258	
FG/SW=1011	+0.5	1000	250	265	274	
FG/SW=1100	+2.5	700	198	214	223	
FG/SW=1101	+2.5	800	215	231	240	
FG/SW=1110	+2.5	900	232	247	256	
FG/SW=1111	+2.5	1000	249	264	273	

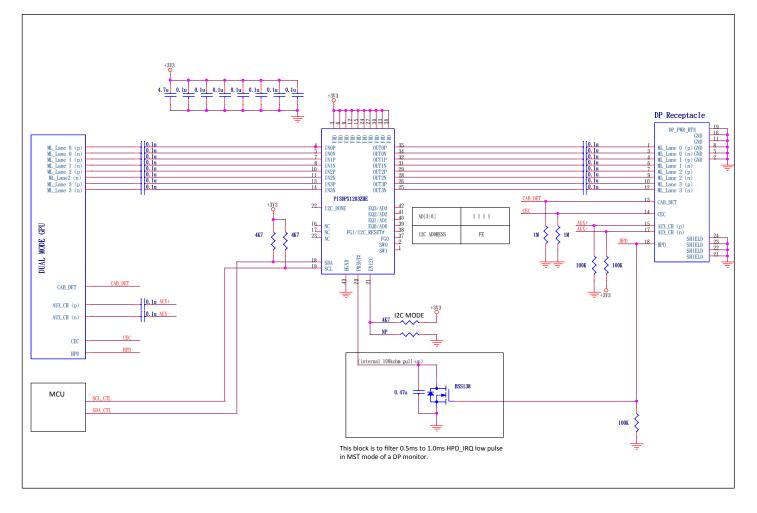




7. Application/Implementation

7.1 Reference Schematic

- Determine the loss profile between a transmitter and a receiver. •
- Based upon the loss profile and signal swing, determine the optimal equalization settings.
- Select appropriate voltage output swing.
- If required, select the correct differential pair polarity.
- To set voltage logic levels on configuration pins, use a 5-k Ω pullup for high level, tie pin to GND for low level, and place a 5-k Ω pullup and 5-k Ω pulldown for HiZ.







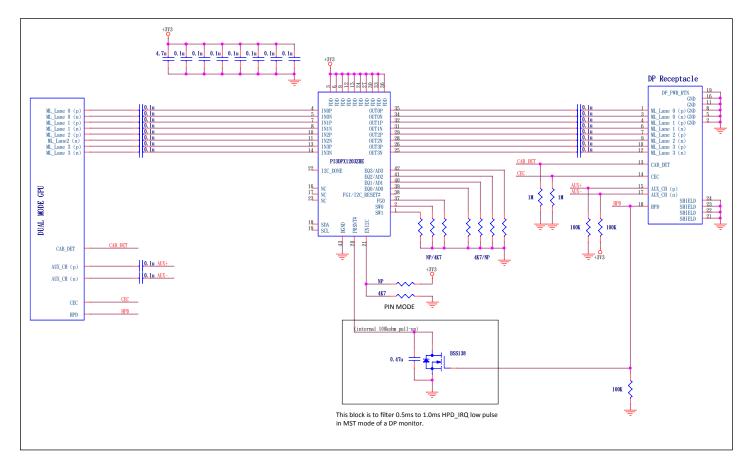


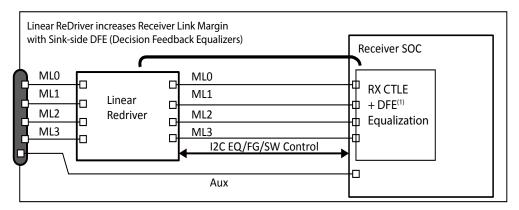
Figure 7-1 Source-side Application Circuit



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PI3DPX1203

7.2 Sink-side Application



Note

(1) The HBR3 receiver equalizer includes a CTLE cascaded with a one-tap adaptive DFE with a feedback coefficient limited to < 50mV. The DFE behavior is described below.

where:

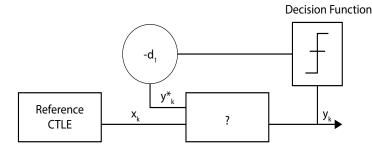
 $y_k = x_k - d_1^* \operatorname{sgn} (y_k - 1)$ y_k is the DFE differential output voltage

 y_k^* is the decision function output voltage

 r_{k} is the differential input voltage after CTLE

d, is the feedback coefficient

k is the UI sample



Reference HBR3 Receiver Equalizer DFE



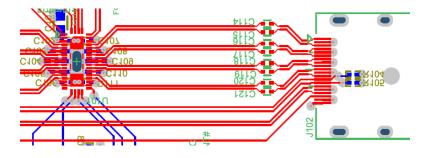
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7.3 Layout Guidelines

As transmission data rate increases rapidly, any flaws and/or mis-matches on PCB layout are amplified in terms of signal integrity. Layout guideline for high-speed transmission is highlighted in this application note.

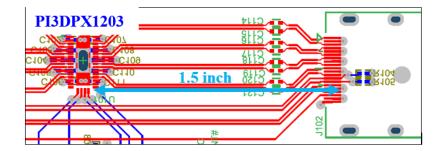
7.3.1 AC coupling Capacitor

Below is an example of placing AC coupling capacitors on high-speed channels.



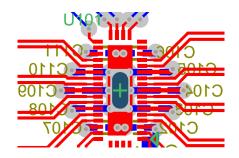
7.3.2 Location

To wisely use the equalization selections offered by PI3DPX1203, it is recommended to place PI3DPX1203 at the end of the entire path. In short, PI3DPX1203 should be located close to the output DP connector in a source application. Below is the PI3DPX1203 placement on its evaluation board.



7.3.3 Thermal Pad GND Via Recommendation

To wisely use the equalization selections offered by PI3DPX1203, it is recommended to place PI3DPX1203 at the end of the entire path. In short, PI3DPX1203 should be located close to the output DP connector in a source application. Below is the PI3DPX1203 placement on its evaluation board.



Several GND vias are the "must" requirement in thermal pad. The recommended Via size is 12/24 mil.





7.3.4 General Power and Ground Guideline

To provide a clean power supply for Pericom high-speed device, few recommendations are listed below:

- Power (VDD) and ground (GND) pins should be connected to corresponding power planes of the printed circuit board directly without passing through any resistor.
- The thickness of the PCB dielectric layer should be minimized such that the VDD and GND planes create low inductance paths.
- One low-ESR 0.1uF decoupling capacitor should be mounted at each VDD pin or should supply bypassing for at most two VDD pins. Capacitors of smaller body size, i.e. 0402 package, is more preferable as the insertion loss is lower. The capacitor should be placed next to the VDD pin.
- One capacitor with capacitance in the range of 4.7uF to 10uF should be incorporated in the power supply decoupling design as well. It can be either tantalum or an ultra-low ESR ceramic.
- A ferrite bead for isolating the power supply for Pericom high-speed device from the power supplies for other parts on the printed circuit board should be implemented.
- Several thermal ground vias must be required on the thermal pad. 25-mil or less pad size and 14-mil or less finished hole are recommended.

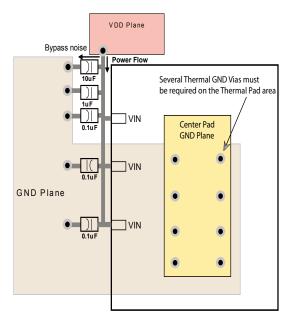


Figure 7-1 Decoupling Capacitor Placement Diagram



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		PI3DPX1203	

7.3.5 High-speed signal Routing

Good-designed layout is essential to prevent signal reflection:

- For 90 Ω differential impedance, width-spacing-width micro-strip of 6-7-6 mils is recommended; for 100 Ω differential impedance, width-spacing-width micro-strip of 5-7-5 mils is recommended.
- Differential impedance tolerance is targeted at $\pm 15\%$.

Trace and board parameters:	Single-ended mode:
Trace width: W= 6.0 🔿 mils	Characteristic impedance:MicrostripStripline20=50.732.9Ω
Trace thickness: t = 1.9 🚔 mils (1.39 oz)	
Trace spacing: S= 7.0 🔿 mils	Capacitance: Co= 2.70 6.30 pf/in
Dielectric (layer) thickness: h= 4.4 🔿 mils (b=10.7 mils)	Delay: Tpd= 137.1 171.6 ps/in
Dielectric (layer) asymmetry: 50	Speed: v= 185.4 148.2 mm/ns
Relative dielectric constant: ≈ 4.11	Differential mode:
	Microstrip Stripline
PCB edge view	Differential impedance: $Z_{0}=$ 90.8 62.4 Ω
	Stripline Zo formula accurate if (W/b)<0.35
↑ ţh b↓ ţh1 *S ** ₩.	3. Stripline Zo formula accurate if (b/t)⊳4
↑ h b ↓h1 Frace and board parameters:	Single-ended mode:
	Single-ended mode: Characteristic Microstrip Stripline
Trace and board parameters:	Single-ended mode: Characteristic impedance: Zo= 55.4 36.7 Ω
Trace and board parameters: Trace width: W= 5.0 mils	Single-ended mode: Characteristic Microstrip Stripline impedance: Zo= 55.4 36.7 Ω Capacitance: Co= 2.47 5.54 pf/in
Trace and board parameters: Trace width: $W = 5.0 \ $ mils Trace thickness: $t = 1.3 \ $ mils (1.39 oz) Trace spacing: $S = 7.0 \ $ mils	Single-ended mode: Microstrip Stripline Characteristic Microstrip Stripline impedance: Zo= 55.4 36.7 Ω Capacitance: Co= 2.47 5.54 pf/in Delay: Tpd= 137.1 171.6 ps/in
Trace and board parameters: Trace width: $W = 5.0 \ \clubsuit \ mils$ Trace thickness: $t = 1.9 \ \clubsuit \ mils$ (1.39 oz) Trace spacing: $S = 7.0 \ \clubsuit \ mils$ Dielectric (layer) thickness: $h = 4.4 \ \clubsuit \ mils$ (b=10.7 mils)	Single-ended mode: Characteristic Microstrip impedance: Zo= 55.4 36.7 Capacitance: Co= 2.47 5.54
Trace and board parameters: Trace width: $W = 5.0 \Rightarrow$ mils Trace thickness: $t = 1.9 \Rightarrow$ mils (1.39 oz) Trace spacing: $S = 7.0 \Rightarrow$ mils Dielectric (layer) thickness: $h = 4.4 \Rightarrow$ mils (b=10.7 mils) Dielectric (layer) asymmetry: $50 \Rightarrow %$ (h1=4.4, h2=4.4)	Single-ended mode: Microstrip Stripline Characteristic Microstrip Stripline impedance: Zo= 55.4 36.7 Ω Capacitance: Co= 2.47 5.54 pf/in Delay: Tpd= 137.1 171.6 ps/in Speed: v= 185.4 148.2 mm/ns
Trace and board parameters: Trace width: $W = 5.0 \ \clubsuit \ mils$ Trace thickness: $t = 1.9 \ \clubsuit \ mils$ (1.39 oz) Trace spacing: $S = 7.0 \ \clubsuit \ mils$ Dielectric (layer) thickness: $h = 4.4 \ \clubsuit \ mils$ (b=10.7 mils)	Single-ended mode:MicrostripStriplineCharacteristic 36.7 Ω Capacitance: $Co=$ 2.47 5.54 pf/in Delay:Tpd= 137.1 171.6 ps/in Speed: $v=$ 185.4 148.2 mm/ns Differential mode:MicrostrinStripline
Trace and board parameters: Trace width: $W = 5.0 \Rightarrow$ mils Trace thickness: $t = 1.9 \Rightarrow$ mils (1.39 oz) Trace spacing: $S = 7.0 \Rightarrow$ mils Dielectric (layer) thickness: $h = 4.4 \Rightarrow$ mils (b=10.7 mils) Dielectric (layer) asymmetry: $50 \Rightarrow %$ (h1=4.4, h2=4.4)	Single-ended mode: Microstrip Stripline Characteristic Microstrip Stripline impedance: Zo= 55.4 36.7 Ω Capacitance: Co= 2.47 5.54 pf/in Delay: Tpd= 137.1 171.6 ps/in Speed: v= 185.4 148.2 mm/ns

Figure 7-2 Trace Width and Clearance of Micro-strip and Strip-line

For micro-strip, using 1/2oz Cu is fine. For strip-line in 6+ PCB layers, 1oz Cu is more preferable.





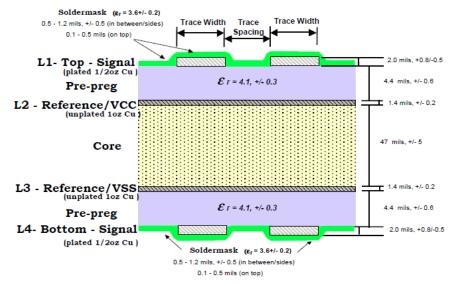


Figure 7-3 4-Layer PCB Stack-up Example

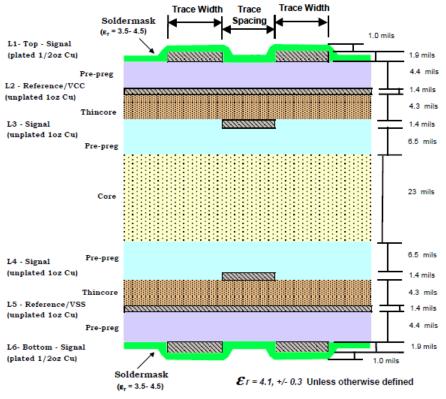


Figure 7-4 6-Layer PCB Stack-up Example

Ground referencing is highly recommended. If unavoidable, stitching capacitors of 0.1uF should be placed when reference plane is changed.





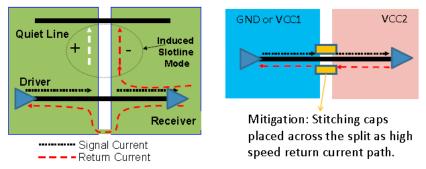


Figure 7-5 Stitching Capacitor Placement

- To keep the reference unchanged, stitching vias must be used when changing layers.
- Differential pair should maintain symmetrical routing whenever possible. The intra-pair skew of micro-strip should be less than 5 mils.
- To keep the reference unchanged, stitching vias must be used when changing layers.
- Differential pair should maintain symmetrical routing whenever possible. The intra-pair skew of micro-strip should be less than 5 mils.

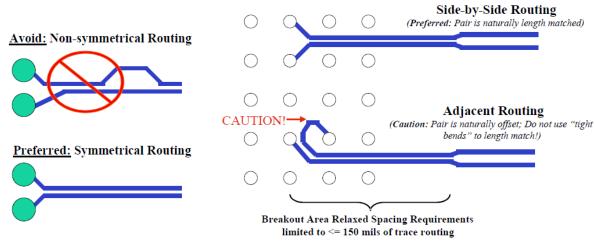


Figure 7-6 Layout Guidance of Matched Differential Pair

- For minimal crosstalk, inter-pair spacing between two differential micro-strip pairs should be at least 20 mils or 4 times the dielectric thickness of the PCB.
- Wider trace width of each differential pair is recommended in order to minimize the loss, especially for long routing. More consistent PCB impedance can be achieved by a PCB vendor if trace is wider.
- Differential signals should be routed away from noise sources and other switching signals on the printed circuit board.
- To minimize signal loss and jitter, tight bend is not recommended. All angles α should be at least 135 degrees. The inner air gap A should be at least 4 times the dielectric thickness of the PCB.





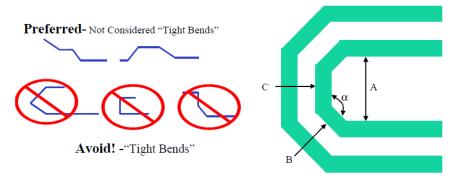


Figure 7-7 Layout Guidance of Bends

Stub creation should be avoided when placing shunt components on a differential pair.

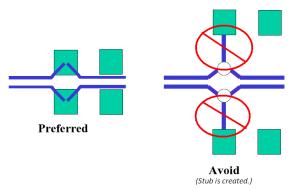


Figure 7-8 Layout Guidance of Shunt Component

Placement of series components on a differential pair should be symmetrical.

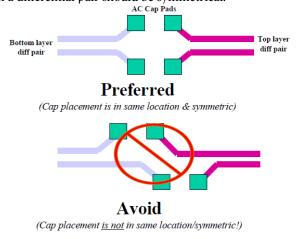


Figure 7-9 Layout Guidance of Series Component

Stitching vias or test points must be used sparingly and placed symmetrically on a differential pair.

•

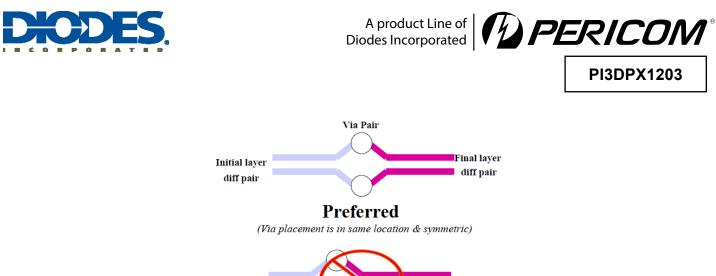




Figure 7-10 Layout Guidance of Stitching Via



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7.4 DP 1.4 CTS Test Report

Internal DisplayPort test setup is shown below for the reference.

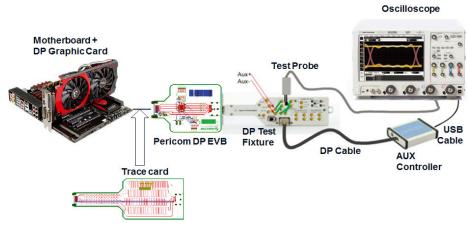


Figure 7-11 Displayport test set-up

Below is application-side trace card insertion loss information.

DP FR4 trace	0 in	6 in	12 in	18 in	24 in	30 in	36 in
Insertion loss @ 8.1Gbps	-8.15 dB	-11.52 dB	-14.88 dB	-17.60 dB	-19.94 dB	-22.92 dB	-28.62 dB





PI3DPX1203 DP1.4 CTS Report

Overall Result: PASS

Test Configuration Details							
Device Description							
Test Specification	1.4						
Lane	4 Lanes						
SSC	Disabled						
	Test Session Details						
DisplayPort Test Controller	UnigrafDPTC						
Fixture Type	Other						
Infiniium SW Version	05.70.00901						
Infiniium Model Number	DSOX92504A						
Infiniium Serial Number	MY54410104						
Application SW Version	3.52.0001						
Debug Mode Used	No						
Compliance Limits (official)	DisplayPort Compliance Test Specification Version 1.4 Official Test Limit						

Summary of Results





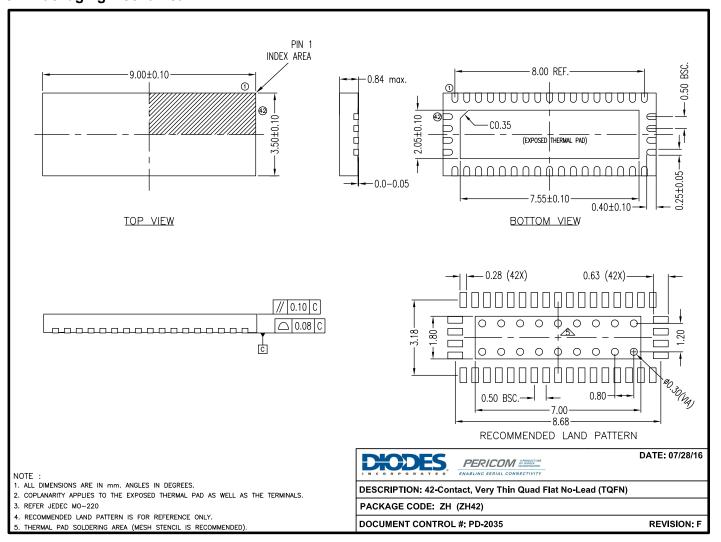
Pass	# Failed	# Trials	Test Name	Worst Actual	Worst Margin	Pass Limits
\checkmark	0	2	3.1 Lane 3 - Eye Diagram Test (TP3 EQ) (HBR2 and HBR3) - HBR2CPAT	0.000	50.0 %	-500 m <= VALUE <= 500 m
\checkmark	0	1	3.1 Lane 3 - Eye Diagram Test with No Cable Model (TP3 EQ) (HBR2 and HBR3) - HBR2CPAT	0.000	50.0 %	-500 m <= VALUE <= 500 m
\checkmark	0	2	3.12 Lane 3 - Total Jitter Test (TP3 EQ) (High Bit Rate 3) - HBR2CPAT	566.000 mUI	12.9 %	VALUE <= 650.000 mUI
\checkmark	0	1	3.12 Lane 3 - Total Jitter Test with No Cable Model (TP3 EQ) (High Bit Rate 3) - HBR2CPAT	626.600 mUI	3.6 %	VALUE <= 650.000 mUI
\checkmark	0	10	3.3 Lane 3 - Peak to Peak Voltage Test - PLTPAT	874 mV	36.7 %	VALUE <= 1.380 V
\checkmark	0	1	3.2 Lane 3 - Non Pre-Emphasis Level Test (Swing 2/Swing 0) - PLTPAT	5.3748 dB	10.3 %	5.2000 dB <= VALUE <= 6.9000 dB
\checkmark	0	1	3.2 Lane 3 - Non Pre-Emphasis Level Test (Swing 2/Swing 1) - PLTPAT	3.0294 dB	24.8 %	1.6000 dB <= VALUE <= 3.5000 dB
√	0	4	3.3 Lane 3 - Pre-Emphasis Level Test (Pre-emphasis 0) - PLTPAT	-3.536 dB	151E+01 %	VALUE <= 250 mdB
\checkmark	0	3	3.3 Lane 3 - Pre-Emphasis Level Delta Test (Pre-emphasis 1 to Pre-emphasis 0) - PLTPAT	2.021 dB	1.1 %	VALUE >= 2.000 dB
\checkmark	0	1	3.3 Lane 3 - Non-Transition Voltage Range Measurement (Swing 2) - PLTPAT	1.007	42.2 %	VALUE >= 708 m
\checkmark	0	2	3.3 Lane 3 - Pre-Emphasis Level Delta Test (Pre-emphasis 2 to Pre-emphasis 1) - PLTPAT	2.304 dB	44.0 %	VALUE >= 1.600 dB
\checkmark	0	1	3.3 Lane 3 - Non-Transition Voltage Range Measurement (Swing 1) - PLTPAT	1.037	46.5 %	VALUE >= 708 m
\checkmark	0	1	3.3 Lane 3 - Pre-Emphasis Level Delta Test (Pre-emphasis 3 to Pre-emphasis 2) - PLTPAT	1.874 dB	17.1 %	VALUE >= 1.600 dB
\checkmark	0	1	3.3 Lane 3 - Non-Transition Voltage Range Measurement (Swing 0) - PLTPAT	1.026	20.7 %	VALUE >= 850 m
√	0	1	3.2 Lane 3 - Non Pre-Emphasis Level Test (Swing 3/Swing 2) - PLTPAT	1.8652 dB	25.4 %	1.0000 dB <= VALUE <= 4.4000 dB





8. Mechanical / Packaging

8.1 Packaging Mechanical







8.2 Part Marking Information

Our standard product mark follows our standard part number ordering information, except for those products with a speed letter code. The speed letter code mark is placed after the package code letter, rather than after the device number as it is ordered. After electrical test screening and speed binning has been completed, we then perform an "add mark" operation which places the speed code letter at the end of the complete part number.

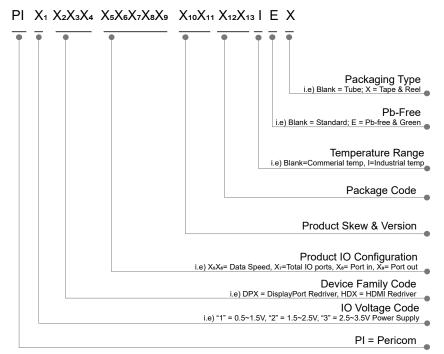


Figure 8-1 Part naming information



YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code

Figure 8-2 Part marking information





8.3 Tape & Reel Materials and Design

Carrier Tape

The Pocketed Carrier Tape is made of Conductive Polystyrene plus Carbon material (or equivalent). The surface resistivity is 106Ohm/ sq. maximum. Pocket tapes are designed so that the component remains in position for automatic handling after cover tape is removed. Each pocket has a hole in the center for automated sensing if the pocket is occupied or not, thus facilitating device removal. Sprocket holes along the edge of the center tape enable direct feeding into automated board assembly equipment. See Figures 3 and 4 for carrier tape dimensions.

Cover Tape

Cover tape is made of Anti-static Transparent Polyester film. The surface resistivity is 107Ohm/Sq. Minimum to 1011Ohm sq. maximum. The cover tape is heat-sealed to the edges of the carrier tape to encase the devices in the pockets. The force to peel back the cover tape from the carrier tape shall be a MEAN value of 20 to 80gm (2N to 0.8N).

Reel

The device loading orientation is in compliance with EIA-481, current version. The loaded carrier tape is wound onto either a 13-inch reel, or 7-inch reel. The reel is made of Antistatic High-Impact Polystyrene. The surface resistivity 10^7 Ohm/sq. minimum to 10^{11} Ohm/sq. max.

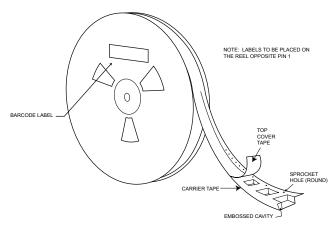


Figure 8-3 Tape & Reel label information

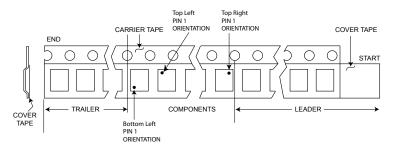


Figure 8-4 Tape leader and trailer pin 1 orientations





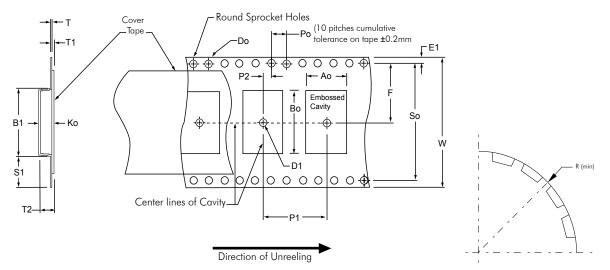


Figure 8-5 Standard embossed carrier tape dimensions

Table 8-1. Constant Dimensions

Tape Size	D0	D1 (Min)	E1	P0	P2	R (See Note 2)	S1 (Min)	T (Max)	T1 (Max)
8mm		1.0			2.0 ± 0.05	25	0.6		
12mm									
16mm	1.5 +0.1	1.5	1.75 ± 0.1 4.0 ± 0.1 30		0.6	0.1			
24mm	-0.0		1.75 ± 0.1	4.0 ± 0.1	2.0 ± 0.1			0.6	0.1
32mm		2.0		50	N/A				
44mm		2.0	2.0 ± 0.15	50	(See Note 3)				

Table 8-2. Variable Dimensions

Tape Size	P ₁	B ₁ (Max)	E ₂ (Min)	F	So	T ₂ (Max.)	W (Max)	A ₀ , B ₀ , & K ₀
8mm	Specific per package type.	4.35	6.25	3.5 ± 0.05		2.5	8.3	
12mm	Refer to FR-0221 (Tape and Reel Packing Information) or	8.2	10.25	5.5 ± 0.05	N/A (see	6.5	12.3	
16mm	visit www.pericom.com/pdf/	12.1	14.25	7.5 ± 0.1	note 4)	8.0	16.3	See Note 1
24mm	gen/tapereel.pdf	20.1	22.25	11.5 ± 0.1		12.0	24.3	See Note 1
32mm		23.0	N/A	14.2 ± 0.1	28.4± 0.1	12.0	32.3	
44mm		35.0	N/A	20.2 ± 0.15	40.4 ± 0.1	16.0	44.3	

NOTES:

1. A0, B0, and K0 are determined by component size. The cavity must restrict lateral movement of component to 0.5mm maximum for 8mm and 12mm wide tape and to 1.0mm maximum for 16,24,32, and 44mm wide carrier. The maximum component rotation within the cavity must be limited to 200 maximum for 8 and 12 mm carrier tapes and 100 maximum for 16 through 44mm.

2. Tape and components will pass around reel with radius "R" without damage.

3. S1 does not apply to carrier width ≥32mm because carrier has sprocket holes on both sides of carrier where Do≥S1.

4. So does not exist for carrier \leq 32mm because carrier does not have sprocket hole on both side of carrier.





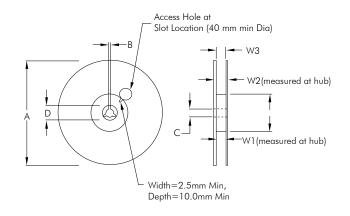


Table 8-3. Reel dimensions by tape size

Tape Size	А	N (Min) See Note A	W1	W2(Max)	W3	B (Min)	С	D (Min)
8mm	178 ±2.0mm or	60 ±2.0mm or 100±2.0mm	8.4 +1.5/-0.0 mm	14.4 mm	Shall Accom- modate Tape Width Without Interference	1.5mm	13.0 +0.5/-0.2 mm	20.2mm
12mm	330±2.0mm		12.4 +2.0/-0.0 mm	18.4 mm				
16mm		m 100 ±2.0mm	16.4 +2.0/-0.0 mm	22.4 mm				
24mm	220 12 0		24.4 +2.0/-0.0 mm	30.4 mm				
32mm	330 ±2.0mm		32.4 +2.0/-0.0 mm	38.4 mm				
44mm			44.4 +2.0/-0.0 mm	50.4 mm				

NOTE:

A. If reel diameter A=178 ±2.0mm, then the corresponding hub diameter (N(min) will by 60 ±2.0mm. If reel diameter A=330±2.0mm, then the corresponding hub diameter (N(min)) will by 100±2.0mm.





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